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June 2014



FQA140N10

N-Channel QFET® MOSFET

100 V, 140 A, 10 m Ω

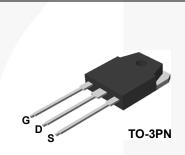
Description

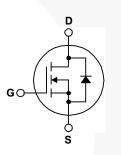
This N-Channel enhancement mode power MOSFET is • 140 A, 100 V, $R_{DS(on)}$ = 10 m Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 220 nC) resistance, and to provide superior switching performance and • Low Crss (Typ. 470 pF) high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor • 100% Avalanche Tested control, and variable switching power applications.

Features

- I_D = 70 A

- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

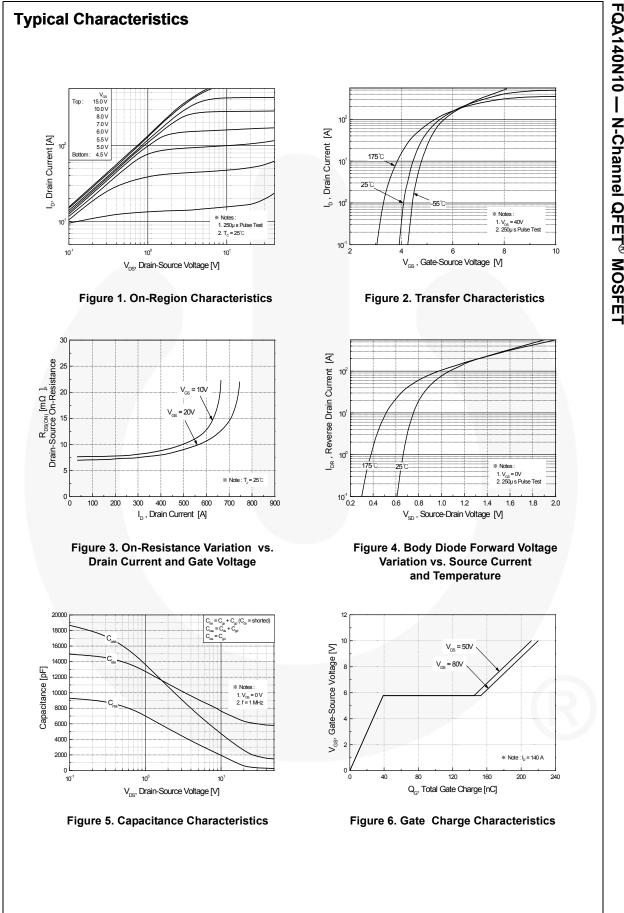
Symbol	Parameter	FQA140N10	Unit
V _{DSS}	Drain-Source Voltage	100	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)	140	A
	- Continuous (T _C = 100°C)	99	A
I _{DM}	Drain Current - Pulsed (Note 1)	560	A
V _{GSS}	Gate-Source Voltage	± 25	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	1500	mJ
I _{AR}	Avalanche Current (Note 1)	140	А
E _{AR}	Repetitive Avalanche Energy (Note 1)	37.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.5	V/ns
PD	Power Dissipation (T _C = 25°C)	375	W
	- Derate above 25°C	2.5	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C
Τ _L	Maximum lead temperature for soldering purposes,1/8" from case for 5 seconds.	300	°C

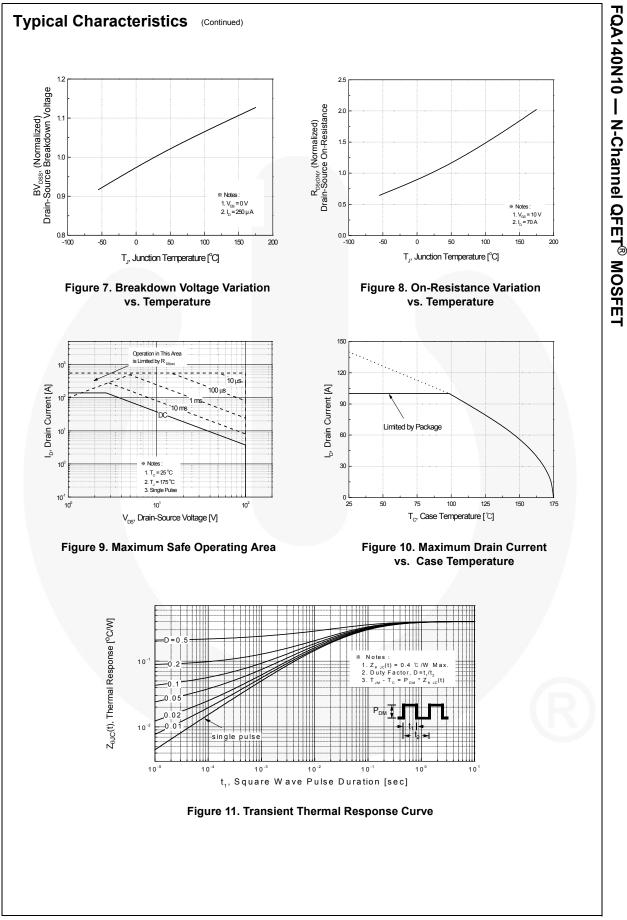
Thermal Characteristics

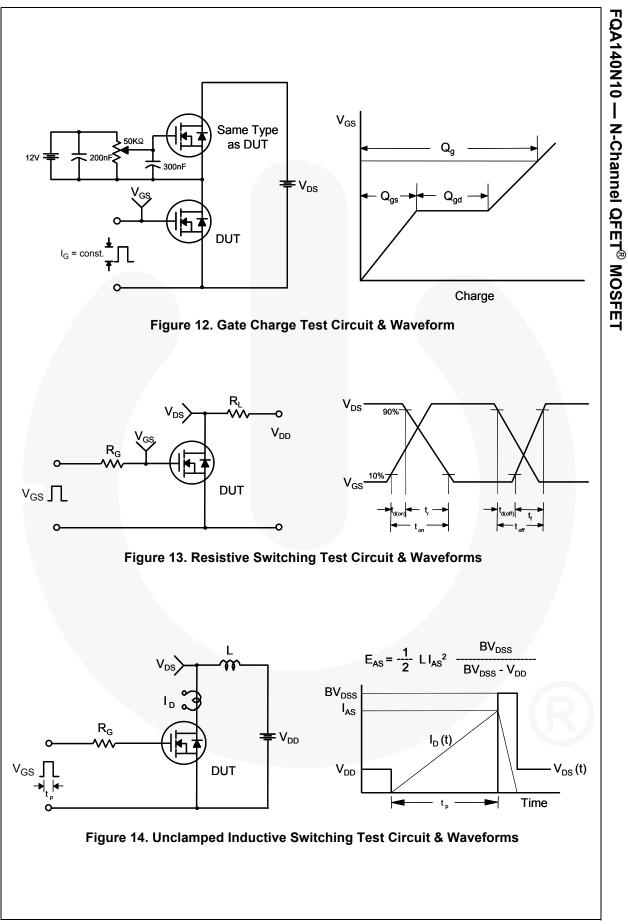
Symbol	Parameter	FQA140N10	Unit	
R _{θJC}	Thermal Resistance, Junction-to-Case, Max.	0.4	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

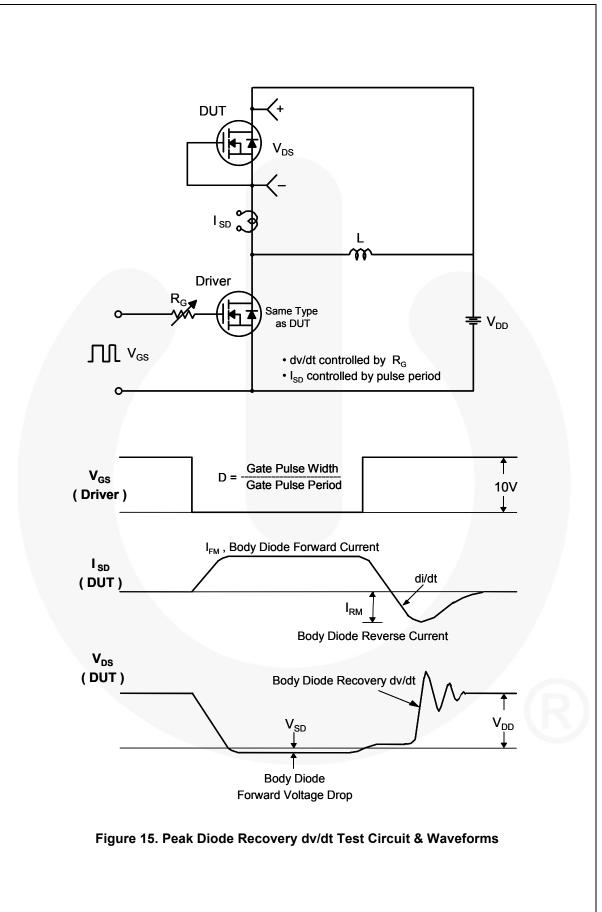
FQA'		•		ckagePacking MethodReelD-3PNTubeN/		Size	Tape Wi	սու	Quantity	
	140N10					/A	N/A		30 units	
lectri	cal Cha	racteristics	T - 25°(nerwise noted.					
Symbol		Parameter	1 _C - 25 (Test Conditions		Min.	Тур.	Max.	Unit
	aracterist			V -	0.1/1 - 050 - 4		100			
BV _{DSS}	Drain-Source Breakdown Voltage		V_{GS} = 0 V, I _D = 250 µA			100			V	
ΔΒV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient		I_D = 250 μ A, Referenced to 25°C				0.08		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current		V _{DS} = 80 V, V _{GS} = 0 V				1	μA		
				$V_{DS} = 64 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$					10	μA
		y Leakage Current, F			$25 V, V_{DS} = 0 V$				100	nA
IGSSR	Gate-Bod	y Leakage Current, F	keverse	V _{GS} =	-25 V, V _{DS} = 0 V				-100	nA
On Cha	racterist	ics								
V _{GS(th)}		shold Voltage	_	V _{DS} =	V _{GS} , I _D = 250 μA		2.0		4.0	V
R _{DS(on)}	Static Dra On-Resist				10 V, I _D = 70 A			0.008	0.01	Ω
9 _{FS}	Forward T	ransconductance	_	V _{DS} =	30 V, I _D = 70 A			80		S
	l		_	50						
Dynam	ic Charao	cteristics	_							
C _{iss}	Input Cap	acitance		V _{DS} =	25 V, V _{GS} = 0 V,			6100	7900	pF
C _{oss}	Output Ca	pacitance		f = 1.0	MHz			2000	2600	pF
C _{rss}	Reverse T	ransfer Capacitance						420	550	pF
Switchi	ing Char	acteristics								
		Delay Time	_					75	160	ns
t _{d(on)} t _r	Turn-On F		_		V _{DD} = 40 V, I _D = 140 A,			940	1890	ns
		Delay Time	-	R _G = 2	5Ω			350	710	ns
t _{d(off)} t _f	Turn-Off F	,		-		(Note 4)		360	730	ns
Q _g	Total Gate			V -	64)(1 - 140)			220	285	nC
∝ _g Q _{gs}		rce Charge		V _{DS} =	64 V, I _D = 140 A,			39		nC
∽ _{gs} Q _{gd}	Gate-Drai			VGS -	10 V	(Note 4)		114		nC
yu	Outo Dia	in onlargo				()				
Drain-S	Source Di	ode Characteris	stics ar	nd Max	imum Ratings	;				
I _S		Continuous Drain-So				(Note 5)			140	Α
I _{SM}	Maximum	Pulsed Drain-Source	e Diode F	orward	Current	, ,			560	Α
V _{SD}	Drain-Sou	rce Diode Forward V	oltage	V _{GS} =	0 V, I _S = 140 A				1.5	V
t _{rr}	Reverse F	Recovery Time		$V_{GS} = 0 V, I_S = 140 A,$ $dI_F / dt = 100 A/\mu s$			140		ns	
Q _{rr}	Reverse F	Recovery Charge					730		nC	
		, ,							1	R
otes: Repetitive ra	iting : pulse-wid	th limited by maximum junct	ion tempera	ature.						
L = 0.115 m	iH, I _{AS} = 140 A,	$V_{DD} = 25 \text{ V}, \text{ R}_{G} = 25 \Omega, \text{ sta}$ μ s, $V_{DD} \leq \text{BV}_{DSS}$ starting	rting $T_J = 2$							

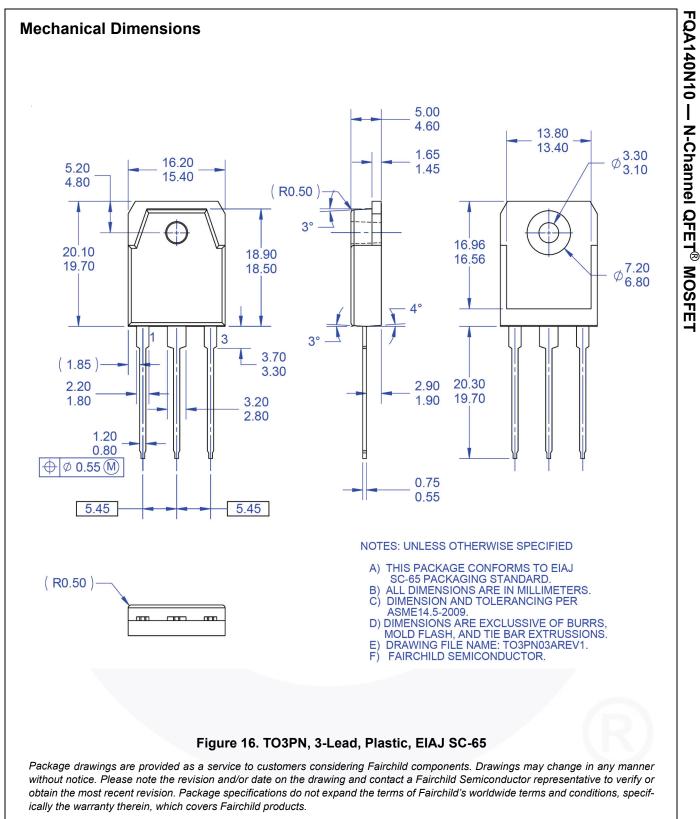
FQA140N10 — N-Channel QFET[®] MOSFET











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http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT3PN-003



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